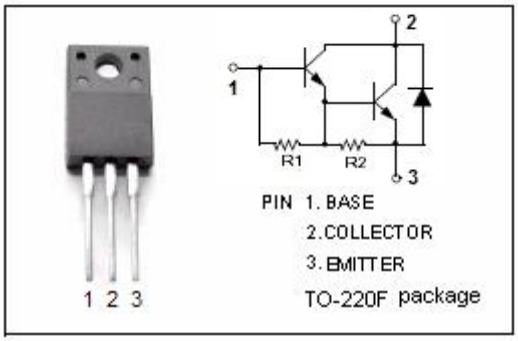
isc Silicon NPN Darlington Power Transistor 2SD2399

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V(Min)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.5V(Max) @I_C= 2A
- High DC Current Gain
  : h_{FE}= 1000(Min) @ I_C= 2A, V_{CE}= 3V
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

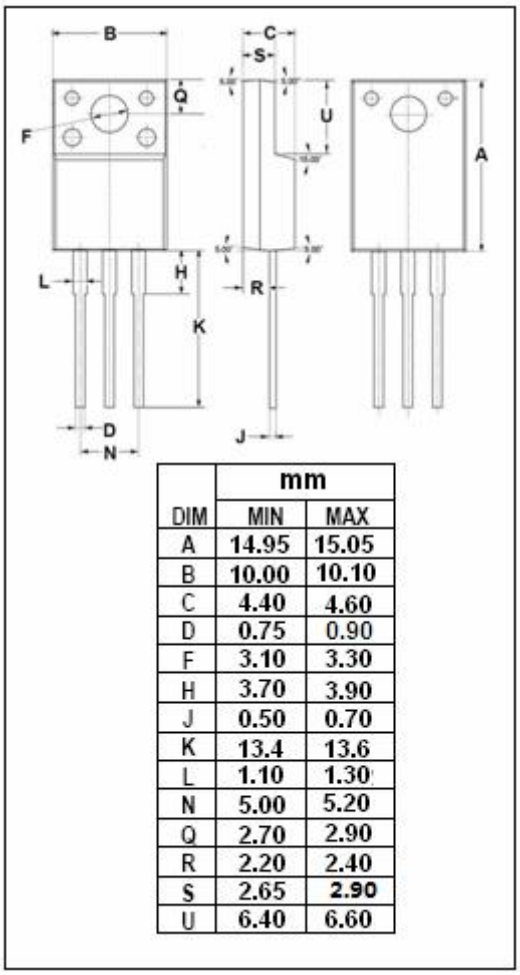


APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	6	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
	Collector Power Dissipation @ T_a=25℃	2.0	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

isc Silicon NPN Darlington Power Transistor 2SD2399

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 50 μ A; I_E= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 4mA			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 80V; I_E= 0			100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			3.0	mA
h_{FE}	DC Current Gain	I_C= 2A; V_{CE}= 3V	1000		10000	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1MHz		35		pF
f_T	Current-Gain—Bandwidth Product	I_E= -0.2A; V_{CE}= 5V, f= 10MHz		40		MHz